

What Is Claimed Is:

1. A circuit comprising:
a MOS transistor having a cap layer comprised of a high dielectric constant material.
2. The circuit of Claim 1 wherein said high dielectric constant material is hafnium silicon oxynitride.
3. The circuit of Claim 1 wherein said MOS transistor is a PMOS transistor.
4. The circuit of Claim 1 wherein said MOS transistor is a NMOS transistor.
5. A MOS transistor comprising:
a cap layer comprised of a high dielectric constant material.
6. The MOS transistor of Claim 5 wherein said high dielectric constant material is hafnium silicon oxynitride.
7. The MOS transistor of Claim 5 wherein said MOS transistor is a NMOS transistor.
8. The MOS transistor of Claim 5 wherein said MOS transistor is a PMOS transistor.
9. A PMOS transistor comprising:
a cap layer comprised of a high dielectric constant material.

10. The PMOS transistor of Claim 9 wherein said high dielectric constant material is hafnium silicon oxynitride.

11. A PMOS transistor comprising:
a cap layer comprised of hafnium silicon oxynitride.